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Reg No.:_

Name:

APJ ABDUL KALAM TECHNOLOGICAL UNIVERSIT Seventh semester B.Tech examinations (S), September 2020

Course Code: EC469

Course Name: OPTOELECTRONIC DEVICES

Max. Marks: 100

Duration: 3 Hours

PART A

		Answer any two full questions, each carries 15 marks.	Marks
1	a)	Explain the different types of absorption mechanisms in semiconductors with	(10)
		neat figures.	
	b)	Differentiate between Franz-keldysh and Stark effects.	(5)
2	a)	Write short notes on Tunneling based lasers.	(7)
	b)	Explain the threshold condition for lasing with mathematical support.	(8)
3	a)	Breifly explain Auger recombination in semiconductors with neat sketches.	(7)
	b)	Distinguish between axial and transverse laser modes.	(8)
		PART B	
		Answer any two full questions, each carries 15 marks.	
4	a)	Explain the working of Raman-Nath modulator with neat diagrams.	(8)
	b)	Explain the principle of white light LED, based on phosphor converters.	(7)
5	a)	Describe the structure and working of InGaN/GaN laser diodes.	(10)
	b)	Discuss the applications of nitride light emitters.	(5)
6	a)	Explain Franz-Keldysh/Stark electro-absorption modulators.	(8)
	b)	Write short notes on optical memory.	(7)
		PART C	
7		Answer any two full questions, each carries 20 marks.	
1	a)	Elucidate working principle of organic LEDs. Mention the properties of	(10)
		material used.	
	b)	Explain the different types of directional couplers used for optical field access	(10)
		with figures.	(10)
8	a)	With neat figures, explain the different types of Wavelength division	(10)
		multiplexer and demultiplexer used for optical field access.	(10)
	b)	Explain the illumination geometry of microcavity photodiode.	(10)

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- 9 a) Elucidate the working principle of optical Add/Drop multiplexors used in optical field access (10)
 - b) Write short notes on Polymer LED.

(5)

c) The quantum efficiency of a RAPD is 80% for detection of radiation at a wavelength of 0.9µm. When incident optical power is 0.5µW, the output current of the device is 11µA. Determine the multiplication factor of the photodiode under this condition.